



(11) **EP 3 316 325 B1**

(12) **EUROPEAN PATENT SPECIFICATION**

(45) Date of publication and mention
of the grant of the patent:
05.06.2019 Bulletin 2019/23

(51) Int Cl.:
H01L 51/42^(2006.01) H01L 51/50^(2006.01)

(21) Application number: **17198262.2**

(22) Date of filing: **25.10.2017**

(54) **QUANTUM DOT LIGHT EMITTING DIODE AND QUANTUM DOT DISPLAY DEVICE INCLUDING THE SAME**

QUANTENPUNKT-LEUCHTDIODE UND QUANTENPUNKT-ANZEIGEVORRICHTUNG DAMIT
DIODE ÉLECTROLUMINESCENTE À POINT QUANTIQUE ET DISPOSITIF D’AFFICHAGE À POINT
QUANTIQUE LA COMPRENANT

(84) Designated Contracting States:
**AL AT BE BG CH CY CZ DE DK EE ES FI FR GB
GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO
PL PT RO RS SE SI SK SM TR**

(30) Priority: **01.11.2016 KR 20160144575**

(43) Date of publication of application:
02.05.2018 Bulletin 2018/18

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Description**CROSS-REFERENCE TO RELATED APPLICATIONS**

5 **[0001]** This application claims priority to and the benefit of Republic of Korea Patent Application No. 10-2016-0144575 filed in the Republic of Korea on November 1, 2016.

BACKGROUND10 **Field of the Disclosure**

[0002] The present disclosure relates to a quantum dot (QD) light emitting diode, and more particularly, to a QD light emitting diode having an excellent hole transporting property and a QD display device including the same.

15 **Description of the Background**

[0003] Recently, as society has entered in earnest upon an information age, a field of display devices that represent all sorts of electrical signals as visual images has been developed rapidly. For example, a flat panel display device, such as a liquid crystal display (LCD) device, a plasma display panel (PDP) device, a field emission display (FED) device, and an organic light emitting diode (OLED) device, has been introduced.

20 **[0004]** On the other hand, use of quantum dots (QD) to display devices has been researched or studied. In the QD, an electron in unstable state transitions from a conduction band to a valence band such that light is emitted. Since the QD has a high extinction coefficient and excellent quantum yield, strong fluorescent light is emitted from the QD. In addition, since the wavelength of the light from the QD is controlled by a size of the QD, entire visible light can be emitted

25 by controlling the size of the QD.

[0005] FIG. 1 is a schematic view illustrating the related art QD light emitting diode.

[0006] As shown in FIG. 1, the QD light emitting diode 10 includes a first electrode 20, a second electrode 80 facing the first electrode 20, a QD emitting material layer (EML) 50 disposed between the first and second electrodes 20 and 80, a hole injection layer (HIL) 30 and a hole transporting layer (HTL) 40 located between the first electrode 20 and the QD EML 50, and an electron transporting layer (ETL) 60 and an electron injection layer (EIL) 70 positioned between the QD EML 50 and the second electrode 80.

[0007] For example, the first electrode 20 serves as an anode, and the second electrode 80 serves a cathode.

[0008] The QD EML 50 includes a plurality of quantum dots.

35 **[0009]** In the QD light emitting diode 10, the hole from the first electrode 20 is transported into the QD EML 50 through the HIL 30 and the HTL 40, and the electron from the second electrode 80 is transported into the QD EML 50 through the EIL 70 and the ETL 60.

[0010] Since the QD has high quantum yield, it is expected that the QD light emitting diode 10 also provides high emitting efficiency. However, the related art QD light emitting diode 10 does not provide the desired emitting efficiency.

40 **[0011]** Document US 2011/0284819 A1 discloses a quantum dot light emitting device comprising spherical semiconductor nano particles in the quantum dot emission layer, for improving the charge transport within said layer.

SUMMARY

[0012] Accordingly, the present disclosure is directed to a QD light emitting according to claim 1.

45 **[0013]** A QD light emitting diode and a QD display device in the present disclosure have an excellent hole transporting property.

[0014] A QD light emitting diode and a QD display device in the present disclosure have excellent emitting efficiency.

[0015] Additional features and advantages of the disclosure will be set forth in the description which follows, and in part will be apparent from the description, or may be learned by practice of the disclosure. The objectives and other advantages of the disclosure will be realized and attained by the structure particularly pointed out in the written description and claims hereof as well as the appended drawings.

50 **[0016]** An aspect of the present disclosure is a quantum dot (QD) light emitting diode including first and second electrodes facing each other; a QD emitting material layer between the first and second electrodes; and a semiconducting member acting as a hole transporting path in the QD emitting material layer.

55 **[0017]** Another aspect of the present disclosure is a quantum dot (QD) display device having a light emitting diode including an anode and a cathode facing each other; a quantum dot emitting material layer between the anode and the cathode; and a hole transporting enhancing member in the quantum dot emitting material layer, wherein the hole transporting enhancing member has a conduction band level between -6.5 and -5.0 eV, and has a shape having an aspect

ratio of at least 2.

[0018] Various embodiments provide a quantum dot (QD) light emitting diode, comprising: first and second electrodes facing each other; a QD emitting material layer between the first and second electrodes; and a semiconducting member acting as a hole transporting path in the QD emitting material layer.

[0019] In one or more embodiments, the QD light emitting diode further comprises: a hole transporting layer between the first electrode and the QD emitting material layer, wherein the semiconducting member has a first end contacting the hole transporting layer.

[0020] In one or more embodiments, the semiconducting member has a second end disposed within the QD emitting material layer. The first and second ends may be opposite ends of the semiconducting member.

[0021] In one or more embodiments, the semiconducting member has a conduction band level being smaller (lower) than a HOMO level of the hole transporting layer and being larger (higher) than a conduction band level of the QD emitting material layer.

[0022] In one or more embodiments, the QD light emitting diode further comprises: an electron transporting layer between the QD emitting material layer and the second electrode, wherein the second end of the semiconducting member is spaced apart from the electron transporting layer.

[0023] In one or more embodiments, one end of the semiconducting member has at least two paths.

[0024] In one or more embodiments, the semiconducting member is disposed to be inclined with respect to at least one of upper and lower surfaces of the QD emitting material layer.

[0025] In one or more embodiments, an upper surface of the QD emitting material layer has a first height from a lower surface of the QD emitting material layer, and the semiconducting member has a second height from the lower surface of the QD emitting material layer, and wherein the second height is smaller than the first height.

[0026] In one or more embodiments, the semiconducting member has a shape having an aspect ratio equal to or greater than 2.

[0027] In one or more embodiments, the semiconducting member includes a plate shape.

[0028] In one or more embodiments, the semiconducting member has a protrusion pattern at a surface.

[0029] In one or more embodiments, the semiconducting member includes at least one of CdSe, CdS, ZnSe, AlAs, GaP and SiC.

[0030] Various embodiments provide a quantum dot display device having a quantum dot light emitting diode according to one or more embodiments described herein, wherein the semiconducting member of the quantum dot light emitting diode has a conduction band level between -6.5 eV and -5.0 eV,

[0031] Various embodiments provide a quantum dot (QD) display device having a light emitting diode, the diode comprising: an anode and a cathode facing each other; a quantum dot emitting material layer between the anode and the cathode; and a hole transporting enhancing member in the quantum dot emitting material layer, wherein the hole transporting enhancing member has a conduction band level between -6.5 eV and -5.0 eV.

[0032] In one or more embodiments, the hole transporting enhancing member has a shape having an aspect ratio of at least 2.

[0033] In one or more embodiments, the QD display device further comprises a hole transporting layer between the anode and the quantum dot emitting material layer.

[0034] In one or more embodiments, the hole transporting layer has a HOMO level greater than the conduction band level of the hole transporting enhancing member and the quantum dot emitting material layer has a conduction band level smaller than the conduction band level of the hole transporting enhancing member.

[0035] In one or more embodiments, an upper surface of the quantum dot emitting material layer has a first height from a lower surface of the quantum dot emitting material layer, and the hole transporting enhancing member has a second height from the lower surface of the quantum dot emitting material layer, and wherein the second height is smaller than the first height.

[0036] In one or more embodiments, the hole transporting enhancing member has one end contacting the hole transporting layer.

[0037] In one or more embodiments, the hole transporting enhancing member has the other end disposed within the QD emitting material layer.

[0038] In one or more embodiments, the hole transporting enhancing member includes at least one of CdSe, CdS, ZnSe, AlAs, GaP and SiC.

[0039] It is to be understood that both the foregoing general description and the following detailed description are examples and are explanatory and are intended to provide further explanation of the disclosure as claimed.

BRIEF DESCRIPTION OF THE DRAWINGS

[0040] The accompanying drawings, which are included to provide a further understanding of the disclosure and are incorporated in and constitute a part of this application, illustrate aspects of the disclosure and together with the description

serve to explain the principles of the disclosure.

[0041] In the drawings:

FIG. 1 is a schematic view illustrating the related art QD light emitting diode;

FIG. 2 is an energy diagram of the related art QD light emitting diode;

FIG. 3 is a schematic circuit diagram of a QD display device according to the present disclosure;

FIG. 4 is a schematic cross-sectional view of a QD display device according to the present disclosure;

FIG. 5 is a schematic cross-sectional view of a QD light emitting diode according to the present disclosure;

FIG. 6 is an energy diagram of a QD light emitting diode according to the present disclosure;

FIGs. 7A to 7D illustrate various shapes of a semiconductor rod; and

FIGs. 8A to 8C are graphs showing emitting properties of a QD light emitting diode according to the present disclosure.

DETAILED DESCRIPTION

[0042] Reference will now be made in detail to aspects of the disclosure, examples of which are illustrated in the accompanying drawings.

[0043] In the related art QD light emitting diode, the hole transporting property is decreased because of an energy level difference between the ETL and QD EML.

[0044] Namely, referring to FIG. 2, which is an energy diagram of the related art QD light emitting diode. Since the energy level difference " ΔL " between the QD EML and the ETL is small, the electron "e-" is easily or efficiently transported from the ETL into the QD EML.

[0045] However, since the energy level difference " ΔH " between the QD EML and the HTL is large, there is a limitation in the hole "h+" transporting from the HTL into the QD EML.

[0046] In addition, the ligand at a surface of the QD serves as a barrier, the hole transporting problem in the related art QD light emitting diode is further serious. Namely, the hole transporting into the QDs in a lower region, which is close to the HTL, of the QD EML is relatively easy, but the hole transporting into the QDs in an upper region, which is far from the HTL, of the QD EML is very difficult.

[0047] Accordingly, in the related art QD light emitting diode, a charge balance is lost, and the emitting efficiency is decreased.

[0048] FIG. 3 is a schematic circuit diagram of a QD display device according to the present disclosure.

[0049] As shown in FIG. 3, in the QD display device, a gate line GL, a data line DL and a power line PL are formed, and a pixel region P is defined by the gate and data lines GL and DL. In the pixel region P, a switching thin film transistor (TFT) Ts, a driving TFT Td, a storage capacitor Cst and a QD light emitting diode D are formed.

[0050] The switching TFT Ts is connected to the gate line GL and the data line DL, and the driving TFT Td and the storage capacitor Cst are connected to the switching TFT Ts and the power line PL. The QD light emitting diode D is connected to the driving TFT Td.

[0051] In the QD display device, when the switching TFT Ts is turned on by a gate signal applied through the gate line GL, a data signal from the data line DL is applied to a gate electrode of the driving TFT Td and an electrode of the storage capacitor Cst through the switching TFT Ts.

[0052] When the driving TFT Td is turned on by the data signal, an electric current is supplied to the QD light emitting diode D from the power line PL through the driving TFT Td. As a result, the QD light emitting diode D emits light. The storage capacitor Cst serves to maintain the voltage of the gate electrode of the driving TFT Td for one frame. Accordingly, the electroluminescent display device displays images.

[0053] FIG. 4 is a schematic cross-sectional view of a QD display device according to the present disclosure.

[0054] As shown in FIG. 4, the QD display device 100 includes a substrate 150, the TFT Td on the substrate 150 and the QD light emitting diode D over the substrate 150 and connected to the TFT Td.

[0055] The substrate 150 may be a glass substrate or a flexible substrate of a metal or a plastic. For example, the substrate 150 may be a polyimide substrate.

[0056] Although not shown, a buffer layer of an inorganic material, e.g., silicon oxide or silicon nitride, may be formed on the substrate 150.

[0057] The TFT Td is connected to the switching TFT Ts (shown in FIG. 3) and includes a semiconductor layer 152, a gate electrode 160, a source electrode 170 and a drain electrode 172.

[0058] The semiconductor layer 152 is formed on the substrate 150. The semiconductor layer 152 may be formed of an oxide semiconductor material or poly-silicon.

[0059] When the semiconductor layer 152 is formed of the oxide semiconductor material, a light-shielding pattern (not shown) may be formed under the semiconductor layer 152. Accordingly, the light to the semiconductor layer 152 is shielded or blocked by the light-shielding pattern such that thermal degradation of the semiconductor layer 152 can be prevented. On the other hand, when the semiconductor layer 152 is formed of the polycrystalline silicon, impurities may

be doped into both sides of the semiconductor layer 152.

[0060] A gate insulating layer 154 is formed on the semiconductor layer 152. The gate insulating layer 154 may be formed of an inorganic insulating material such as silicon oxide or silicon nitride.

[0061] A gate electrode 160, which is formed of a conductive material, e.g., metal, is formed on the gate insulating layer 154 to correspond to a center portion of the semiconductor layer 152.

[0062] In FIG. 4, the gate insulating layer 154 is formed on the entire surface of the substrate 150. Alternatively, the gate insulating layer 154 may be patterned to have the same shape as the gate electrode 160.

[0063] An interlayer insulating layer 162, which is formed of an insulating material, is formed on the entire surface of the substrate 150 including the gate electrode 160. The interlayer insulating layer 162 may be formed of an inorganic insulating material, e.g., silicon oxide or silicon nitride, or an organic insulating material, e.g., benzocyclobutene or photoacryl.

[0064] The interlayer insulating layer 162 includes first and second contact holes 164 and 166 exposing both sides of the semiconductor layer 152. The first and second contact holes 164 and 166 are positioned at both sides of the gate electrode 160 to be spaced apart from the gate electrode 160.

[0065] In FIG. 4, the first and second contact holes 164 and 166 extend into the gate insulating layer 154. Alternatively, when the gate insulating layer 154 is patterned to have the same shape as the gate electrode 160, there may be no first and second contact holes 164 and 166 in the gate insulating layer 154.

[0066] A source electrode 170 and a drain electrode 172, which are formed of a conductive material, e.g., metal, are formed on the interlayer insulating layer 162. The source electrode 170 and the drain electrode 172 are spaced apart from each other with respect to the gate electrode 160 and respectively contact both sides of the semiconductor layer 152 through the first and second contact holes 164 and 166. The source electrode 170 is connected to the power line PL (shown in FIG. 3).

[0067] The TFT Td including the semiconductor layer 152, the gate electrode 160, the source electrode 170 and the drain electrode 172 serves as a driving element.

[0068] The gate electrode 160, the source electrode 170 and the drain electrode 172 are positioned over the semiconductor layer 152. Namely, the TFT Td has a coplanar structure.

[0069] Alternatively, in the TFT Td, the gate electrode may be positioned under the semiconductor layer, and the source and drain electrodes may be positioned over the semiconductor layer such that the TFT Td may have an inverted staggered structure. In this instance, the semiconductor layer may be formed of amorphous silicon.

[0070] On the other hand, the switching TFT Ts (shown in FIG. 3) may have substantially the same structure as the TFT Td.

[0071] A passivation layer 174, which includes a drain contact hole 176 exposing the drain electrode 172 of the TFT Td, is formed to cover the TFT Td.

[0072] A first electrode 110, which is connected to the drain electrode 172 of the TFT Td through the drain contact hole 176, is separately formed on the passivation layer 174 in each pixel region. The first electrode 110 may be an anode and may be formed of a conductive material having a relatively high work function. For example, the first electrode 110 may be formed of a transparent conductive material such as indium-tin-oxide (ITO) and indium-zinc-oxide (IZO).

[0073] When the QD display device 100 of the present disclosure is a top-emission type, a reflection electrode or a reflection layer may be formed under the first electrode 110. For example, the reflection electrode or the reflection layer may be formed of an aluminum-palladium-copper (APC) alloy.

[0074] A bank layer 115, which covers edges of the first electrode 110, is formed on the passivation layer 174. The bank 115 exposes a center region of the first electrode 110 in the pixel region.

[0075] An emitting layer 130 is formed on the first electrode 110. The emitting layer 130 will be explained in more detail.

[0076] A second electrode 140 is formed on the emitting layer 130 over the substrate 150. The second electrode 140 is positioned at the entire surface of the display area. The second electrode 140 may be a cathode and may be formed of a conductive material having a relatively low work function. For example, the second electrode 140 may be formed of one of aluminum (Al), magnesium (Mg) and an Al-Mg alloy.

[0077] The first electrode 110, the emitting layer 130 and the second electrode 140 constitute the QD light emitting diode D.

[0078] In the QD light emitting diode D of the present disclosure, a QD EML in the emitting layer 130 may include a semiconductor rod such that a hole transporting property is improved. As a result, the emitting efficiency of the QD light emitting diode D and the QD display device 100 is also improved.

[0079] FIG. 5 is a schematic cross-sectional view of a QD light emitting diode according to the present disclosure.

[0080] As shown in FIG. 5, the QD light emitting diode D includes the first electrode 110, the second electrode 140 facing the first electrode 110, a QD emitting material layer (EML) 230 between the first and second electrodes 110 and 140 and a semiconductor rod 240 (semiconducting member or hole transporting enhancing member) in the QD EML 230. The semiconductor rod 240 can be arranged to be inclined with respect to a surface (a lower surface or an upper surface) of the QD EML 230. Namely, the semiconductor rod 240 is not parallel or perpendicular to a surface of the QD

EML 230.

[0081] The first electrode 110 may be an anode, and the second electrode 140 may be a cathode.

[0082] The QD EML 230 may include a plurality of QDs 232. The QD 232 may include a semiconductor material.

[0083] The QD 232 may include a core at a center region and a shell covering the core. The light is emitted from the core. In addition, a ligand for dispersing the QD 232 in the solvent may be combined at a surface of the shell. The core and the shell have a difference in an energy band gap.

[0084] The QD 232 may be formed of a nano-size semiconductor material of II-VI group element or III-V group element. For example, the nano-size semiconductor material may be one of CdSe, CdS, CdTe, ZnSe, ZnTe, ZnS, HgTe, InAs, InP and GaAs.

[0085] In addition, the QD light emitting diode D may further include a hole transporting layer (HTL) 220 between the QD EML 230 and the first electrode 110. One end of the semiconductor rod 240 contacts the HTL 220, and the other end of the semiconductor rod 240 is positioned in the QD EML 230.

[0086] In other words, from the lower surface of the QD EML 230, the upper surface of the QD EML 230 has a first height H1, and the semiconductor rod 240 has a second height H2 being smaller than the first height H1.

[0087] The hole in the HTL 220 is directly transported into the QD EML 230 or is transported into the QD EML 230 through the semiconductor rod 240. Namely, the one end of the semiconductor rod 240 contacts the HTL 220 to serve as a hole transporting path. As a result, the hole is efficiently transported into a center region and an upper region of the QD EML 230 as well as the lower region of the QD EML 230.

[0088] The semiconductor rod 240 has a conduction band being smaller than the highest occupied molecular orbital (HOMO) level of the HTL 220 and being larger than the conduction band (or the HOMO level) of the QD EML 230. For example, the semiconductor rod 240 may include at least one of CdSe, CdS, ZnSe, AlAs, GaP and SiC. The conduction band of the semiconductor rod 240 is listed in Table 1.

Table 1

	Conduction Band Level
CdSe	-5.8 eV
CdS	-6.2 eV
ZnSe	-6.1eV
AlAs	-5.6 eV
GaP	-5.6 eV
SiC	-6.0 eV

[0089] As shown in Table 1, the semiconductor rod 240 has the conduction band level of -6.5 to -5.0eV.

[0090] As a result, an energy barrier between the HTL 220 and the QD EML 230 is reduced, and the hole transporting property into the QD EML 230 is improved.

[0091] FIG. 6 illustrates an energy diagram of a QD light emitting diode according to the present disclosure.

[0092] As shown in FIG. 6, the semiconductor rod 240 has a conduction band being smaller than the HOMO level of the HTL and being larger than the conduction band (or the HOMO level) of the QD EML. Since the hole "h⁺" is transported into the QD EML via a relatively small energy gap " $\Delta H1$ " between the HTL and the semiconductor rod 240 and a relatively small energy gap " $\Delta H2$ " between the semiconductor rod 240 and the QD EML, the hole mobility is improved.

[0093] On the other hand, the electron "e⁻" transporting from an electron transporting layer (ETL) into the QD EML is not blocked by the semiconductor rod 240. Accordingly, in the QD light emitting diode D, the charge balance is improved, and the emitting efficiency is increased.

[0094] Referring back to FIG. 5, the semiconductor rod 240 has a major axis and a minor axis. Namely, the semiconductor rod 240 has an aspect ratio being greater than 1. Further, the aspect ratio of the semiconductor rod 240 can be greater than 2. For example, the aspect ratio of the semiconductor rod 240 may be 2 to 10.

[0095] When the aspect ratio of the semiconductor rod 240 is too small, an area of the HTL 220 covered by the semiconductor rod 240 is increased. In addition, the other end of the semiconductor rod 240 is positioned in a center region of the QD EML 230. As a result, there is a limitation in the hole transporting into the QD 232 in the upper region of the QD EML 230.

[0096] The QD light emitting diode D may further include the ETL 250 between the QD EML 230 and the second electrode 140. In this instance, the semiconductor rod 240 may be spaced apart from the ETL 250.

[0097] Namely, the one end of the semiconductor rod 240 contacts the HTL 220, and the other end of the semiconductor rod 240 is spaced apart from ETL 250.

[0098] When the semiconductor rod 240 contacts the ETL 250, the hole from the HTL 220 is transported into the ETL 250 through the semiconductor rod 240 such that the hole does not participate in the emission of the QD EML 230. However, in the QD light emitting diode D of the present disclosure, since the semiconductor rod 240 is spaced apart from the ETL 250, the emitting efficiency of the QD light emitting diode D is further increased.

[0099] FIGs. 7A to 7D illustrate various shapes of a semiconductor rod.

[0100] As shown in FIG. 7A, the semiconductor rod 240 has a cylinder shape having a major axis and a minor axis. In this instance, one end of the cylinder-shaped semiconductor rod 240 may contact the HTL 220 (shown in FIG. 5), and the other end of the cylinder-shaped semiconductor rod 240 may be spaced apart from the ETL 250 (shown in FIG. 5). Alternatively, the cross-section of the semiconductor rod 240 may have a rectangular (or square) shape such that the semiconductor rod 240 may have a rectangular (or square) pillar shape.

[0101] As shown in FIG. 7B, the semiconductor rod 240 may include protrusion patterns 242 at the surface. As a result, the hole transporting property into the QD 232 (shown in FIG. 5) in the center region of the QD EML 230 is improved. For example, a density of the protrusion patterns 242 in the center portion of the semiconductor rod 240 may be higher than that in the ends of the semiconductor rod 240.

[0102] As shown in FIG. 7C, the semiconductor rod 240 may have a plate shape.

[0103] As shown in FIG. 7D, one end of the semiconductor rod 240 may be branched such that at least two hole transporting paths may be provided at the one end of the semiconductor rod 240. Namely, the semiconductor rod 240 has a branched-end 244. The branched-end 244 may contact the HTL 220 (shown in FIG. 5) such that the hole transporting from the HTL 220 into the semiconductor rod 240 may be improved. Alternatively, the branched-end 244 may be positioned in the QD EML 230 (shown in FIG. 5) such that the hole transporting from the HTL 220 into the QD EML 230 is improved.

[0104] In the present disclosure, when the "rod" has a major axis and a minor axis, there is no limitation in a shape. The major axis of the semiconductor rod 240 is inclined to the surface of the HTL 220, and one end of the major axis of the semiconductor rod 240 is positioned in the QD EML 230.

[0105] Referring back to FIG. 5, the QD light emitting diode D may further include a hole injection layer (HIL) 210 between the first electrode 110 and the HTL 220 and an electron injection layer (EIL) 260 between the second electrode 140 and the ETL 250.

[0106] The HIL 210, the HTL 220, the QD EML 230, the semiconductor rod 240, the ETL 250 and the EIL 260 constitute the emitting layer 130.

[0107] For example, the HIL 210 may be formed of one of poly(3,4-ethylenedioxythiophene) polystyrene sulfonate (PEDOT:PSS), and the HTL 220 may include at least one of N,N'-diphenyl-N,N'-bis(3-methylphenyl)-1,1'-biphenyl-4,4'-diamine (TPD), poly(9-vinylcarbazole) (PVK), 4,4'-N, N'-dicarbazole-biphenyl (CBP), N,N'-bis(naphthalene-1-yl)-N,N'-bis(phenyl)benzidine (α -NPD) and 4,4',4''-tris(N-carbazolyl)-triphenylamine (TCTA). The ETL 250 may be formed of at least one of 2,2',2''-(1,3,5-benzinetriyl)-tris(1-phenyl-1-H-benzimidazole) (TPBi) and 3-(4-biphenyl)-4-phenyl-5-butyl-phenyl-1,2,4-triazole (TAZ), and the EIL 260 may include LiF. However, there is no limitation in a material of the HIL 210, the HTL 220, the ETL 250 and the EIL 260.

QD light emitting diode

[0108] The QD light emitting diode including the first electrode of ITO, the HIL of PEDOT:PSS, the HTL of p-TPD and PVK, the semiconductor rod of CdSe, the QD EML of InP QDs (red emission), the ETL of TPBi, the EIL of LiF and the second electrode of Al is manufactured.

[0109] The emitting property of the QD light emitting diode is listed in Table 2 and shown in FIGs. 8A to 8C.

Table 2

	Turn On				Max			
	Volt (V)	J (mA/cm ²)	EQE	Cd/m ²	Volt (V)	J (mA/cm ²)	EQE	Cd/m ²
Ref	21	1.65	0.085	1.12	28	87.01	0.025	12.01
Ex	15	1.30	0.137	1.69	22	100.37	0.104	82.75

[0110] As shown in Table 2 and FIGs. 8A to 8C, in comparison to the QD light emitting diode (Ref), which does not include the semiconductor rod, the emitting property of the QD light emitting diode (Ex), which includes the semiconductor rod, is substantially improved. In addition, as shown in FIG. 8A, the semiconductor rod does not participate in the emission (no color shift).

[0111] As mentioned above, the QD light emitting diode D includes the semiconductor rod 240, which is positioned in the QD EML 230 to serve as a hole transporting path, such that the charge balance in the QD light emitting diode D is

improved.

[0112] In addition, one end of the semiconductor rod 240 contacts the HTL 220, and the other end of the semiconductor rod 240 is positioned in the QD EML 230 to be spaced apart from the ETL 250. As a result, the hole transporting property into the QD EML 230 is uniformed and improved.

[0113] Accordingly, the emitting efficiency of the QD light emitting diode D and the QD display device 100 is improved.

[0114] It will be apparent to those skilled in the art that various modifications and variations can be made in the aspects of the disclosure without departing from the scope of the disclosure. Thus, it is intended that the present disclosure covers the modifications and variations of this disclosure provided they come within the scope of the appended claims.

Claims

1. A quantum dot light emitting diode (D), comprising:

first and second electrodes (110, 140) facing each other;
a quantum dot emitting material layer (230) between the first and second electrodes (110, 140); and
a semiconducting member (240) in the quantum dot emitting layer (230), **characterized in that** the semiconducting member (240) has a shape including a major axis and a minor axis, wherein the major axis extends between a first end and a second end of the semiconducting member (240), wherein the semiconductor member (240) provides a hole transporting path in the quantum dot emitting material layer (230), wherein the aspect ratio of the shape is 2 or greater.

2. The quantum dot light emitting diode (D) according to claim 1, further comprising:
a hole transporting layer (220) between the first electrode (110) and the quantum dot emitting material layer (230).

3. The quantum dot light emitting diode (D) according to claim 2, wherein the first end of the semiconducting member (240) contacts the hole transporting layer (220).

4. The quantum dot light emitting diode (D) according to claim 2 or 3, wherein the semiconducting member (240) has a valence band level being lower than a HOMO level of the hole transporting layer (220) and being higher than a valence band level of the quantum dot emitting material layer (230).

5. The quantum dot light emitting diode (D) according to any one of claims 1 to 4, wherein the second end of the semiconducting member (240) is disposed within the quantum dot emitting material layer (230).

6. The quantum dot light emitting diode (D) according to claim 5, further comprising:
an electron transporting layer (250) between the quantum dot emitting material layer (230) and the second electrode (140), wherein the second end of the semiconducting member (240) is spaced apart from the electron transporting layer (250).

7. The quantum dot light emitting diode (D) according to any one of claims 1 to 6, wherein one end (244) of the semiconducting member (240) is a branched end that has at least two paths.

8. The quantum dot light emitting diode (D) according to any one of claims 1 to 7, wherein the semiconducting member (240) is disposed to be inclined with respect to at least one of upper and lower surfaces of the quantum dot emitting material layer (230).

9. The quantum dot light emitting diode (D) according to any one of claims 1 to 8, wherein an upper surface of the quantum dot emitting material layer (230) has a first height (H1) from a lower surface of the quantum dot emitting material layer (230), and the semiconducting member (240) has a second height (H2) from the lower surface of the quantum dot emitting material layer (230), and wherein the second height (H2) is smaller than the first height (H1).

10. The quantum dot light emitting diode (D) according to any one of claims 1 to 9, wherein the aspect ratio is in the range from 2 to 10.

11. The quantum dot light emitting diode (D) according to any one of claims 1 to 10, wherein the semiconducting member (240) includes a plate shape.

12. The quantum dot light emitting diode (D) according to any one of claims 1 to 11, wherein the semiconducting member (240) has a protrusion pattern (242) at a surface.
13. The quantum dot light emitting diode (D) according to any one of claims 1 to 12, wherein the semiconducting member (240) includes at least one of CdSe, CdS, ZnSe, AlAs, GaP and SiC.
14. The quantum dot light emitting diode (D) according to any one of claims 1 to 13, wherein the first electrode (110) is an anode and the second electrode (140) is a cathode.
15. A quantum dot display device having a quantum dot light emitting diode (D) according to any one of claims 1 to 14, wherein the semiconducting member (240) of the quantum dot light emitting diode (D) has a valence band level between -6.5 eV and 5.0 eV.

Patentansprüche

1. Eine Quantenpunkt-Leuchtdiode (D), aufweisend:

eine erste und eine zweite Elektrode (110, 140), die sich gegenüberliegen;
eine Quantenpunktemissionsmaterialschicht (230) zwischen der ersten und zweiten Elektrode (110, 140); und
ein Halbleiterelement (240) in der Quantenpunktemissionsmaterialschicht (230), **dadurch gekennzeichnet, dass** das Halbleiterelement (240) eine Form hat, die eine Hauptachse und eine Nebenachse enthält, wobei sich die Hauptachse zwischen einem ersten Ende und einem zweiten Ende des Halbleiterelements (240) erstreckt, wobei das Halbleiterelement (240) einen Lochtransportpfad in der Quantenpunktemissionsmaterialschicht (230) bereitstellt, wobei das Aspektverhältnis der Form 2 oder größer ist.

2. Die Quantenpunkt-Leuchtdiode (D) gemäß Anspruch 1, ferner aufweisend:
eine Lochtransportschicht (220) zwischen der ersten Elektrode (110) und der Quantenpunktemissionsmaterialschicht (230).
3. Die Quantenpunkt-Leuchtdiode (D) gemäß Anspruch 2, wobei das erste Ende des Halbleiterelements (240) die Lochtransportschicht (220) kontaktiert.
4. Die Quantenpunkt-Leuchtdiode (D) gemäß Anspruch 2 oder 3, wobei das Halbleiterelement (240) ein Valenzbandniveau hat, das niedriger als ein HOMO-Niveau der Lochtransportschicht (220) ist und höher als ein Valenzbandniveau der Quantenpunktemissionsmaterialschicht (230) ist.
5. Die Quantenpunkt-Leuchtdiode (D) gemäß einem der Ansprüche 1 bis 4, wobei das zweite Ende des Halbleiterelements (240) innerhalb der Quantenpunktemissionsmaterialschicht (230) angeordnet ist.
6. Die Quantenpunkt-Leuchtdiode (D) gemäß Anspruch 5, ferner aufweisend:
eine Elektronentransportschicht (250) zwischen der Quantenpunktemissionsmaterialschicht (230) und der zweiten Elektrode (140), wobei das zweite Ende des Halbleiterelements (240) von der Elektronentransportschicht (250) beabstandet ist.
7. Die Quantenpunkt-Leuchtdiode (D) gemäß einem der Ansprüche 1 bis 6, wobei ein Ende (244) des Halbleiterelements (240) ein verzweigtes Ende ist, das mindestens zwei Pfade hat.
8. Die Quantenpunkt-Leuchtdiode (D) gemäß einem der Ansprüche 1 bis 7, wobei das Halbleiterelement (240) so angeordnet ist, dass es in Bezug auf mindestens eine von einer Oberseite und einer Unterseite der Quantenpunktemissionsmaterialschicht (230) geneigt ist.
9. Die Quantenpunkt-Leuchtdiode (D) gemäß einem der Ansprüche 1 bis 8, wobei eine Oberseite der Quantenpunktemissionsmaterialschicht (230) eine erste Höhe (H1) von einer Unterseite der Quantenpunktemissionsmaterialschicht (230) hat und das Halbleiterelement (240) eine zweite Höhe (H2) von der Unterseite der Quantenpunktemissionsmaterialschicht (230) hat und wobei die zweite Höhe (H2) kleiner ist als die erste Höhe (H1).

10. Die Quantenpunkt-Leuchtdiode (D) gemäß einem der Ansprüche 1 bis 9, wobei das Aspektverhältnis in dem Bereich von 2 bis 10 ist.
- 5 11. Die Quantenpunkt-Leuchtdiode (D) gemäß einem der Ansprüche 1 bis 10, wobei das Halbleiterelement (240) eine Plattenform enthält.
12. Die Quantenpunkt-Leuchtdiode (D) gemäß einem der Ansprüche 1 bis 11, wobei das Halbleiterelement (240) ein Vorsprungmuster (242) an einer Oberfläche hat.
- 10 13. Die Quantenpunkt-Leuchtdiode (D) gemäß einem der Ansprüche 1 bis 12, wobei das Halbleiterelement (240) mindestens eines aus CdSe, CdS, ZnSe, AlAs, GaP und SiC enthält.
14. Die Quantenpunkt-Leuchtdiode (D) gemäß einem der Ansprüche 1 bis 13, wobei die erste Elektrode (110) eine Anode ist und die zweite Elektrode (140) eine Kathode ist.
- 15 15. Eine Quantenpunkt-Anzeige-Vorrichtung, die eine Quantenpunkt-Leuchtdiode (D) gemäß einem der Ansprüche 1 bis 14 hat, wobei das Halbleiterelement (240) der Quantenpunkt-Leuchtdiode (D) ein Valenzbandniveau zwischen -6,5 eV und -5,0 eV hat.

Revendications

1. Diode électroluminescente à points quantiques (D), comprenant :

25 des première et deuxième électrodes (110, 140) se faisant mutuellement face ;
une couche de matériau émetteur à points quantiques (230) entre les première et deuxième électrodes (110, 140) ; et
un composant semi-conducteur (240) dans la couche émettrice à points quantiques (230),

30 **caractérisée en ce que** le composant semi-conducteur (240) a une forme comprenant un grand axe et un petit axe, le grand axe s'étendant entre une première extrémité et une deuxième extrémité du composant semi-conducteur (240), le composant semi-conducteur (240) fournissant un trajet de transport de trou dans la couche de matériau émetteur à points quantiques (230), le facteur de forme de la forme étant de 2 ou plus.

- 35 2. Diode électroluminescente à points quantiques (D) selon la revendication 1, comprenant en outre :
une couche de transport de trous (220) entre la première électrode (110) et la couche de matériau émetteur à points quantiques (230).

- 40 3. Diode électroluminescente à points quantiques (D) selon la revendication 2, dans laquelle la première extrémité du composant semi-conducteur (240) vient en contact avec la couche de transport de trous (220).

4. Diode électroluminescente à points quantiques (D) selon la revendication 2 ou 3, dans laquelle le composant semi-conducteur (240) a un niveau de bande de valence étant inférieur à un niveau HOMO de la couche de transport de trous (220) et étant supérieur à une bande de valence de la couche de matériau émetteur à points quantiques (230).

- 45 5. Diode électroluminescente à points quantiques (D) selon l'une quelconque des revendications 1 à 4, dans laquelle la deuxième extrémité du composant semi-conducteur (240) est disposée dans la couche de matériau émetteur à points quantiques (230).

- 50 6. Diode électroluminescente à points quantiques (D) selon la revendication 5, comprenant en outre :
une couche de transport d'électrons (250) entre la couche de matériau émetteur à points quantiques (230) et la deuxième électrode (140), la deuxième extrémité du composant semi-conducteur (240) étant espacée de la couche de transport d'électrons (250).

- 55 7. Diode électroluminescente à points quantiques (D) selon l'une quelconque des revendications 1 à 6, dans laquelle une extrémité (244) du composant semi-conducteur (240) est une extrémité ramifiée qui comporte au moins deux trajets.

8. Diode électroluminescente à points quantiques (D) selon l'une quelconque des revendications 1 à 7, dans laquelle le composant semi-conducteur (240) est disposé de façon à être incliné par rapport à au moins l'une parmi les surfaces supérieure et inférieure de la couche de matériau émetteur à points quantiques (230).
- 5 9. Diode électroluminescente à points quantiques (D) selon l'une quelconque des revendications 1 à 8, dans laquelle une surface supérieure de la couche de matériau émetteur à points quantiques (230) a une première hauteur (H1) depuis une surface inférieure de la couche de matériau émetteur à points quantiques (230), et le composant semi-conducteur (240) a une deuxième hauteur (H2) depuis la surface inférieure de la couche de matériau émetteur à points quantiques (230), et la deuxième hauteur (H2) étant inférieure à la première hauteur (H1).
- 10 10. Diode électroluminescente à points quantiques (D) selon l'une quelconque des revendications 1 à 9, dans laquelle le facteur de forme est dans la plage de 2 à 10.
- 15 11. Diode électroluminescente à points quantiques (D) selon l'une quelconque des revendications 1 à 10, dans laquelle le composant semi-conducteur (240) comprend une forme de plaque.
12. Diode électroluminescente à points quantiques (D) selon l'une quelconque des revendications 1 à 11, dans laquelle le composant semi-conducteur (240) a un motif saillant (242) au niveau d'une surface.
- 20 13. Diode électroluminescente à points quantiques (D) selon l'une quelconque des revendications 1 à 12, dans laquelle le composant semi-conducteur (240) comprend au moins l'un parmi CdSe, CdS, ZnSe, AlAs, GaP et SiC.
14. Diode électroluminescente à points quantiques (D) selon l'une quelconque des revendications 1 à 13, dans laquelle la première électrode (110) est une anode et la deuxième électrode (140) est une cathode.
- 25 15. Dispositif d'affichage à points quantiques comportant une diode électroluminescente à points quantiques (D) selon l'une quelconque des revendications 1 à 14, dans lequel le composant semi-conducteur (240) de la diode électroluminescente à points quantiques (D) a un niveau de bande de valence compris entre -6,5 eV et -5,0 eV.

FIG. 1
RELATED ART

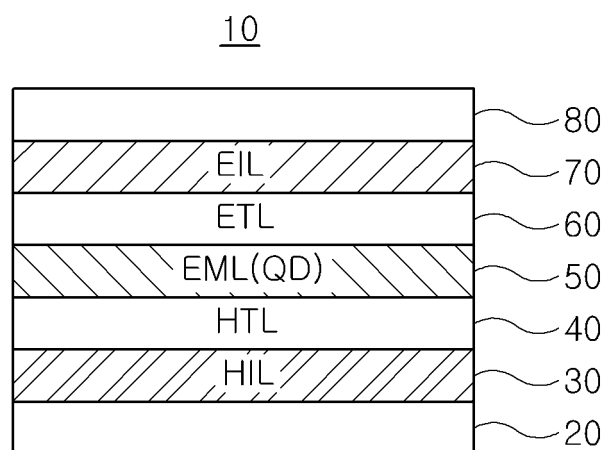


FIG. 2

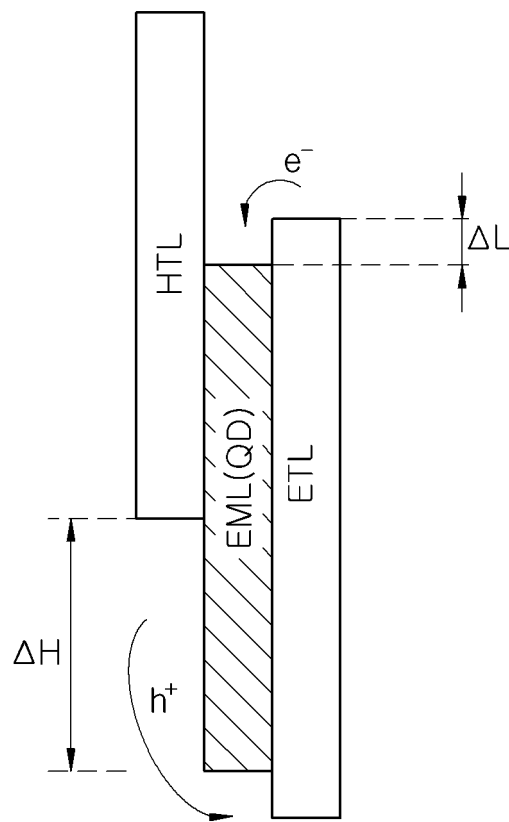


FIG. 3

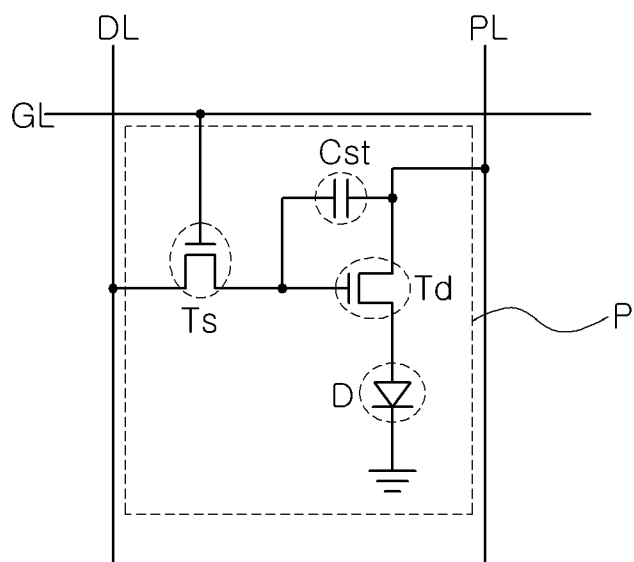


FIG. 4

100

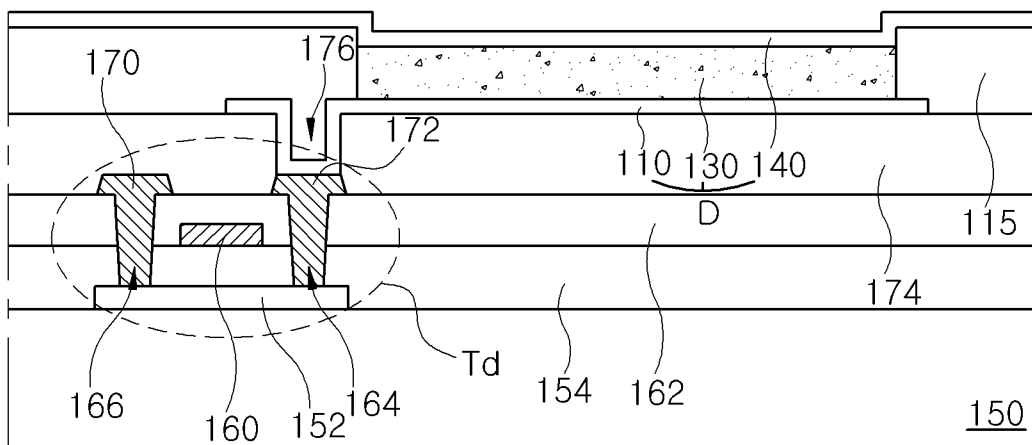


FIG. 5

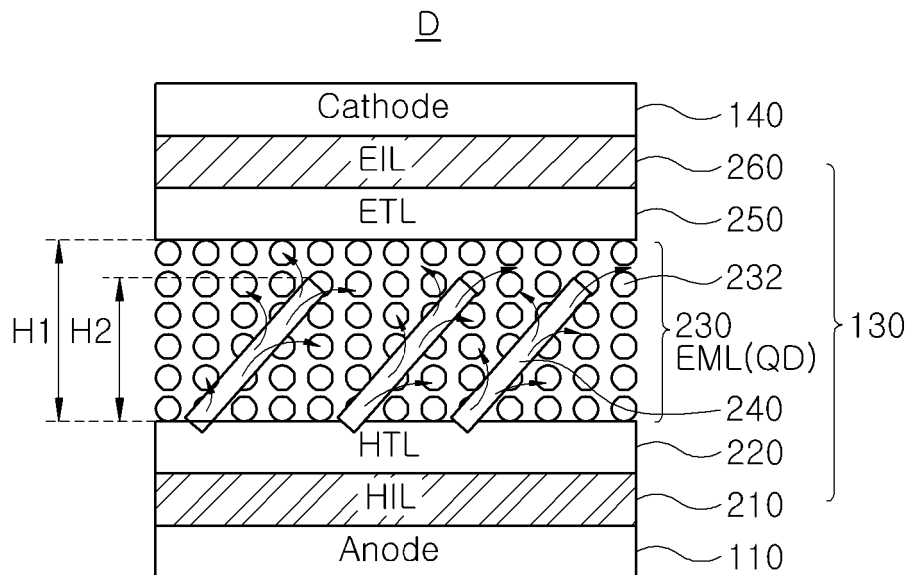


FIG. 6

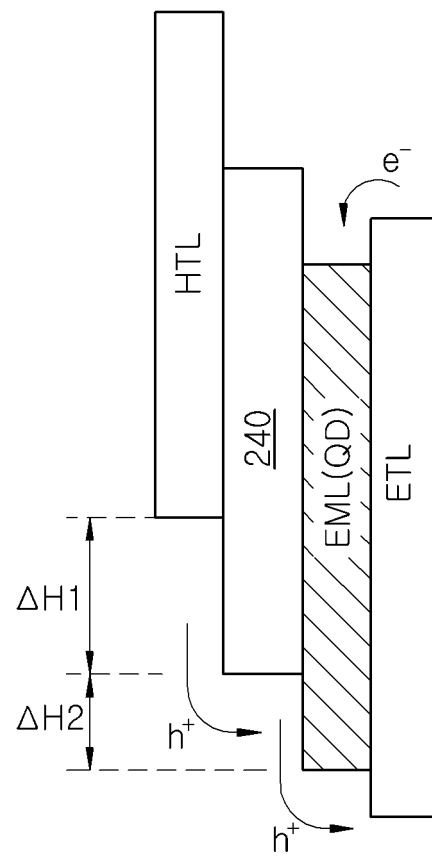


FIG. 7A

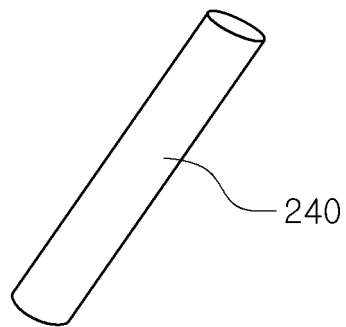


FIG. 7B

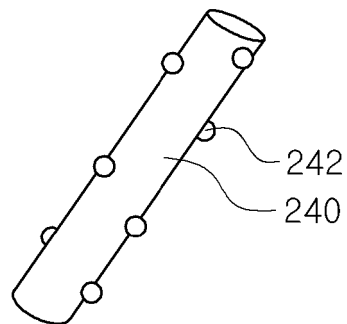


FIG. 7C

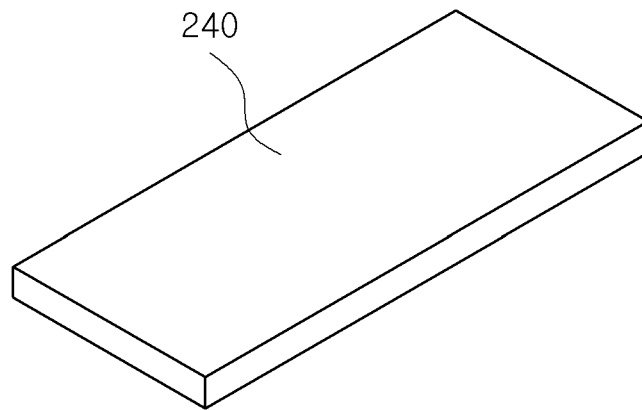


FIG. 7D

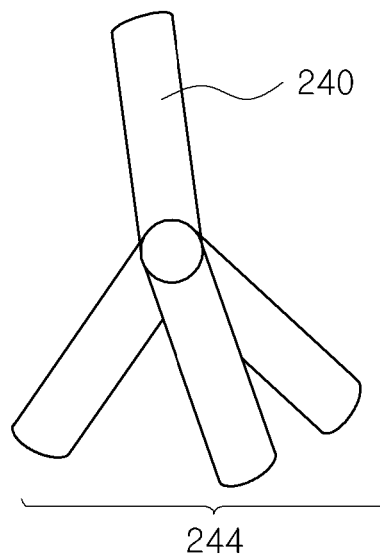


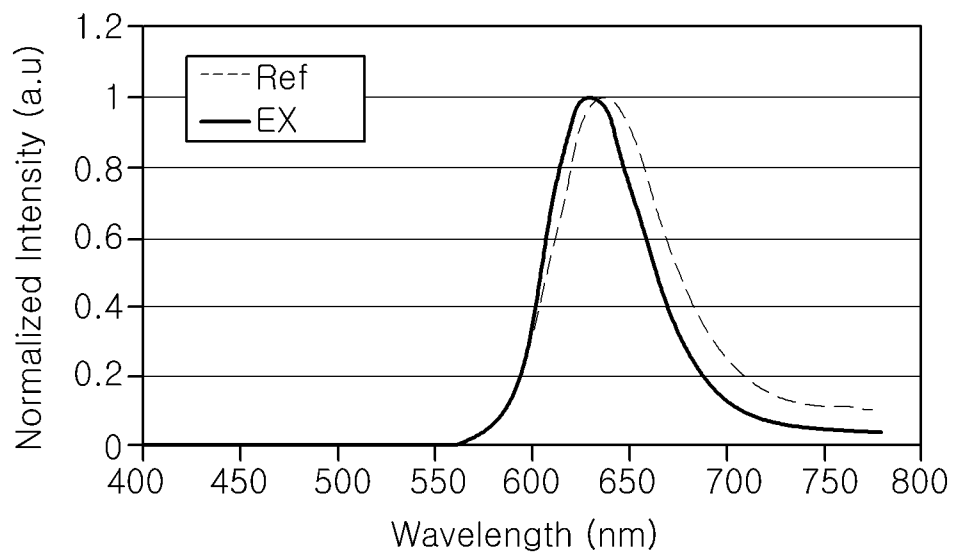
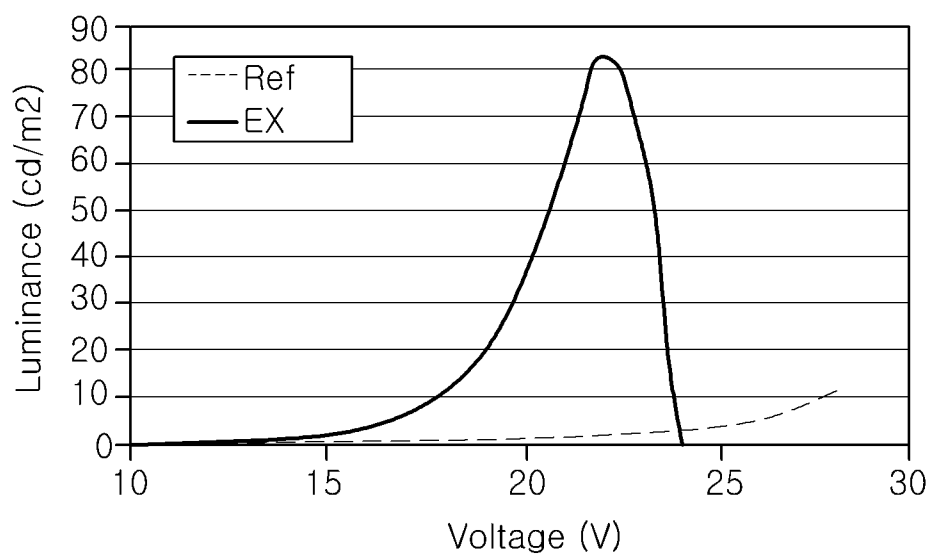
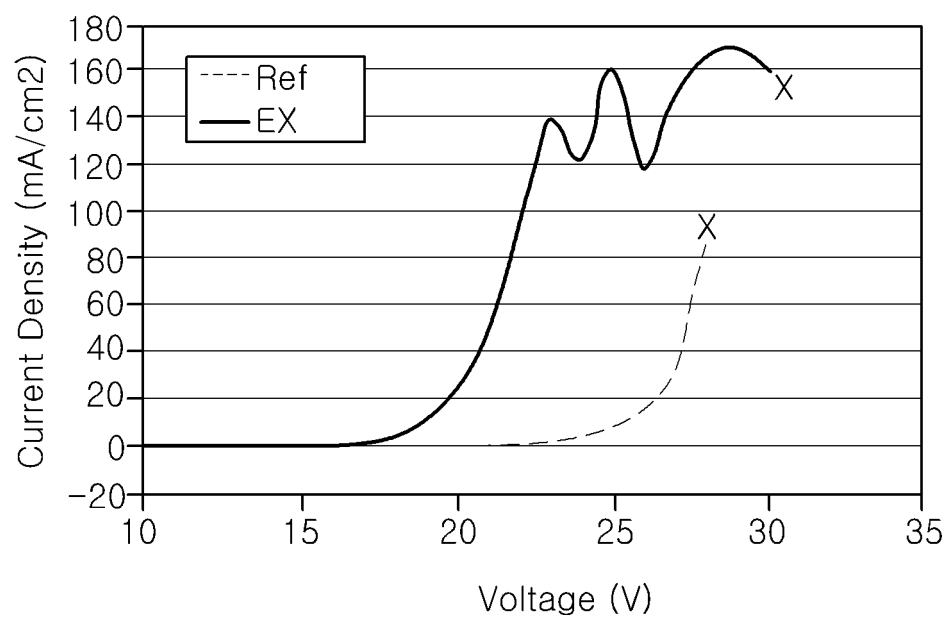
FIG. 8A**FIG. 8B**

FIG. 8C



REFERENCES CITED IN THE DESCRIPTION

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Patent documents cited in the description

- KR 1020160144575 [0001]
- US 20110284819 A1 [0011]

专利名称(译)	量子点发光二极管和包括其的量子点显示装置		
公开(公告)号	EP3316325B1	公开(公告)日	2019-06-05
申请号	EP2017198262	申请日	2017-10-25
[标]申请(专利权)人(译)	乐金显示有限公司		
申请(专利权)人(译)	LG DISPLAY CO. , LTD.		
当前申请(专利权)人(译)	LG DISPLAY CO. , LTD.		
[标]发明人	LEE TAE YANG KIM KYU NAM WOO SUNG IL		
发明人	LEE, TAE-YANG KIM, KYU-NAM WOO, SUNG-IL		
IPC分类号	H01L51/42 H01L51/50		
CPC分类号	H01L51/502 H01L51/5056 H01L51/426 H01L51/4266 Y02E10/549 G02B6/0023 G02F1/1336 H01L27/3246 H01L27/3262 H01L51/5012 H01L51/5072		
优先权	1020160144575 2016-11-01 KR		
其他公开文献	EP3316325A1		
外部链接	Espacenet		

摘要(译)

一种量子点 (QD) 发光二极管 (D) , 包括彼此面对的第一和第二电极 (110,140) ;第一和第二电极 (110,140) 之间的QD发射材料层 (230) ;并且提供了用作QD发光材料层 (230) 中的空穴传输路径的半导体构件 (240) 。

FIG. 1 RELATED ART

10

